







#### CD54HC164, CD74HC164, CD54HCT164, CD74HCT164 SCHS155D - NOVEMBER 1998 - REVISED MARCH 2022

# CDx4HC164, CDx4HCT164 High-Speed CMOS Logic 8-Bit Serial-In/Parallel-Out Shift

Register

#### 1 Features

- **Buffered** inputs
- Asynchronous reset
- Typical  $f_{MAX}$  = 60 MHz at  $V_{CC}$  = 5 V,  $C_L$  = 15 pF,  $T_A = 25 \,^{\circ}C$
- Fanout (over temperature range)
  - Standard Outputs: 10 LSTTL loads
  - Bus driver outputs: 15 LSTTL loads
- Wide operating temp range : 55 °C to 125 °C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- HC types
  - 2 V to 6 V operation
  - High noise immunity :  $N_{IL}$  = 30%,  $N_{IH}$  = 30% of  $V_{CC}$  at  $V_{CC} = 5 V$
- · HCT types
  - 4.5 V to 5.5 V operation
  - Direct LSTTL input logic compatibility,  $V_{II} = 0.8$  $V (Max), V_{IH} = 2 V (Min)$
  - CMOS input compatibility,  $I_1 \le 1 \mu A$  at  $V_{OI}$ ,  $V_{OH}$

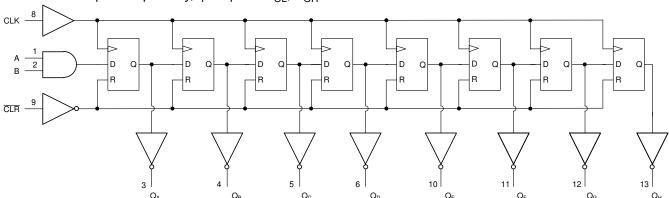
#### 2 Description

The 'HC164 and 'HCT164 are 8-bit serial-in parallelout shift registers with asynchronous reset. Data is shifted on the positive edge of Clock (CLK). A LOW on the Reset (CLR) pin resets the shift register and all outputs go to the LOW state regardless of the input conditions. Two Serial Data inputs (A and B) are provided, either one can be used as a Data Enable control.

#### **Device Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)
CD74HC164M	SOIC (14)	8.65 mm × 3.90 mm
CD74HCT164M	SOIC (14)	8.65 mm × 3.90 mm
CD74HC164E	PDIP (14)	19.31 mm × 6.35 mm
CD74HCT164E	PDIP (14)	19.31 mm × 6.35 mm
CD54HC164F	CDIP (14)	19.55 mm × 6.71 mm

For all available packages, see the orderable addendum at the end of the data sheet.



**Functional Block Diagram** 



#### **Table of Contents**

resiptionon History	1	7.2 Functional Block Diagram	
on History			
		8 Power Supply Recommendations	
onfiguration and Functions		9 Layout	
fications		9.1 Layout Guidelines	
osolute Maximum Ratings	4	10 Device and Documentation Support	
ecommended Operating Conditions	4	10.1 Documentation Support	. 11
nermal Information	4	10.2 Receiving Notification of Documentation Updates	
ectrical Characteristics	5	10.3 Support Resources	
erequisite for Switching Characteristics		10.4 Trademarks	11
vitching Characteristics	7	10.5 Electrostatic Discharge Caution	11
neter Measurement Information		10.6 Glossary	
ed Description	9		
/erview		Information	. 11
vitching Characteristics neter Measurement Informationed Description	7 8 9	10.5 Electrostatic Discharge Caution 10.6 Glossary	

#### 3 Revision History

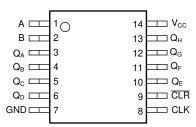
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

#### Changes from Revision C (August 2003) to Revision D (March 2022)

Page



## **4 Pin Configuration and Functions**



J, D, and N Package 14-Pin CDIP, SOIC, and PDIP Top View



#### **5 Specifications**

#### **5.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	(V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> )		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	$(V_O < 0 \text{ or } V_O > V_{CC})$		±20	mA
Io	Continuous output current	$(V_O = 0 \text{ to } V_{CC})$		±25	mA
	Continuous current through V <sub>C</sub>	C or GND		±50	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **5.2 Recommended Operating Conditions**

	-		MIN	MAX	UNIT
V	Supply voltage range	HC types	2	6	V
V <sub>CC</sub>	Supply voltage range	HCT types	4.5	5.5	V
V <sub>I</sub> , V <sub>O</sub>	Input or output voltage		0	V <sub>CC</sub>	V
		2 V		1000	
	Input rise and fall time	4.5 V		500	ns
		6 V		400	
T <sub>A</sub>	Temperature range	·	<b>–</b> 55	125	°C

#### 5.3 Thermal Information

		D (SOIC)	N (PDIP)	
THERMAL METRI	С	14 PINS	14 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)</sup>	86	80	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.



#### **5.4 Electrical Characteristics**

	PARAMETER	TEST	V 00	25℃			–40°C to	85℃	–55℃ to	UNIT	
	PARAMETER	CONDITIONS <sup>(1)</sup>	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII
HC TY	PES .										
			2	1.5			1.5		1.5		
$V_{IH}$	High level input voltage		4.5	3.15			3.15		3.15		V
	Volkage		6	4.2			4.2		4.2		
			2			0.5		0.5		0.5	
$V_{IL}$	Low level input voltage		4.5			1.35		1.35		1.35	V
	Volkago		6			1.8		1.8		1.8	
		$I_{OH} = -20 \mu A$	2	1.9			1.9		1.9		
	High level output voltage	I <sub>OH</sub> = – 20 μA	4.5	4.4			4.4		4.4		
$V_{OH}$	voitage	I <sub>OH</sub> = – 20 μA	6	5.9			5.9		5.9		V
	High level output	I <sub>OH</sub> = – 4 mA	4.5	3.98			3.84		3.7		
	voltage	I <sub>OH</sub> = – 5.2 mA	6	5.48			5.34		5.2		
		I <sub>OL</sub> = 20 μA	2			0.1		0.1		0.1	
	Low level output	I <sub>OL</sub> = 20 μA	4.5			0.1		0.1		0.1	
$V_{OL}$	voltage	I <sub>OL</sub> = 20 μA	6			0.1		0.1		0.1	V
	Low level output	I <sub>OL</sub> = 4 mA	4.5			0.26		0.33		0.4	
	voltage	I <sub>OL</sub> = 5.2 mA	6			0.26		0.33		0.4	V
I <sub>I</sub>	Input leakage current		6			±0.1		±1		±1	μA
I <sub>CC</sub>	Supply current	$V_I = V_{CC}$ or GND	6			8		80		160	μA
	YPES										
V <sub>IH</sub>	High level input voltage		4.5 to 5.5	2			2		2		V
V <sub>IL</sub>	Low level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
.,	High level output voltage	I <sub>OH</sub> = – 20 μA	4.5	4.4			4.4		4.4		V
V <sub>OH</sub>	High level output voltage	I <sub>OH</sub> = – 4 μA	4.5	3.98			3.84		3.7		V
	Low level output voltage	I <sub>OL</sub> = 20 μA	4.5			0.1		0.1		0.1	
V <sub>OL</sub>	Low level output voltage	I <sub>OL</sub> = 4 μA	4.5			0.26		0.33		0.4	V
l <sub>l</sub>	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND	5.5			±0.1		±1		±1	μA
I <sub>CC</sub>	Supply current	$V_I = V_{CC}$ or GND	5.5			8		80		160	μA
		Date Shift-In (1,2)	4.5 to 5.5		100	108		135		147	μA
ΔI <sub>CC</sub> (2) (3)	Additional supply current per input pin	CLR	4.5 to 5.5		100	324		405		441	μA
		CLK	4.5 to 5.5		100	252		315		343	μΑ

<sup>(1)</sup> 

 $V_I = V_{IH}$  or  $V_{IL}$ , unless otherwise noted. This is the increase in supply current for each input that is at one of the specified TTL voltage levels, rather than 0 V or  $V_{CC}$ . (2) (3)

Inputs held at V<sub>CC</sub> – 2.1.



## 5.5 Prerequisite for Switching Characteristics

	DADAMETED	V 00	25°C	;	– 40°C to	85°C	- 55°C to 125°C		UNIT
	PARAMETER	V <sub>CC</sub> (V)	MIN	MAX	MIN	MAX	MIN	MAX	UNII
HC TY	PES	<u>'</u>							
		2	6		5		4		MHz
$f_{MAX}$	Maximum clock frequency	4.5	30		24		20		MHz
		6	35		28		24		MHz
		2	60		75		90		ns
$t_W$	CLR pulse width	4.5	12		15		18		ns
		6	10		13		15		ns
		2	80		100		120		ns
t <sub>w</sub>	CLK pulse width	4.5	16		20		24		ns
		6	14		17		20		ns
		2	60		75		90		ns
$t_{SU}$	Set-up time	4.5	12		15		18		ns
		6	10		13		15		ns
		2	4		4		4		ns
t <sub>H</sub>	Hold time	4.5	4		4		4		ns
		6	4		4		4		ns
		2	80		100		120		ns
$t_{REM}$	CLR to clock, Removal time	4.5	16		20		24		ns
	Temoval unic	6	14		17		20		ns
HCT T	YPES								
f <sub>MAX</sub>	Maximum clock frequency	4.5	27		22		18		MHz
t <sub>W</sub>	CLR pulse width	6	18		23		27		ns
t <sub>W</sub>	CLK pulse width	4.5	18		23		27		ns
t <sub>SU</sub>	Set-up time	6	12		15		18		ns
t <sub>H</sub>	Hold time	4.5	4		4		4		ns
t <sub>REM</sub>	CLR to clock, Removal time	6	16		20		24		ns



## **5.6 Switching Characteristics**

Input  $t_r$ ,  $t_f$  = 6ns.  $C_L$  = 50pF unless otherwise noted

	PARAMETER	V <sub>CC</sub> (V)	25°C		- 40°C to 85°C	– 55°C to 125°C	UNIT
			TYP	MAX	MAX	MAX	
HC TYPES						•	
		2		170	212	255	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	CLK to Q	4.5	14 <sup>(3)</sup>	34	43	51	ns
		6		29	36	43	ns
		2		140	175	210	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	CLR to Q	4.5	11 <sup>(3)</sup>	28	35	42	ns
		6		24	30	36	ns
		2		75		110	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Output transition times	4.5		15		22	ns
		6		13		19	ns
f <sub>MAX</sub>	Maximum clock frequency	5	60 <sup>(3)</sup>				ns
C <sub>IN</sub>	Input capacitance			10	10	10	pF
C <sub>PD</sub>	Power dissipation capacitance <sup>(1)</sup> (2)	5	47				pF
HCT TYPE	S					1	
	CLK to Q	4.5		36	45	54	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	CLK to Q	5	15 <sup>(3)</sup>				
	CLD to O	4.5		38	46	57	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	CLR to Q	5	16 <sup>(3)</sup>				
t <sub>TLH</sub> , t <sub>THL</sub>	Output Transition time	4.5		15	19	22	ns
C <sub>IN</sub>	Input Capacitance						pF
f <sub>MAX</sub>	Maximum clock frequency		54 <sup>(4)</sup>				MHz
C <sub>PD</sub>	Power dissipation capacitance <sup>(1)</sup> (2)	5	49	10	10	10	pF

 <sup>(1)</sup> C<sub>PD</sub> is used to determine the dynamic power consumption, per device.
 (2) P<sub>D</sub> = V<sub>CC</sub> <sup>2</sup>f<sub>i</sub> + Σ (C<sub>L</sub> V<sub>CC</sub> <sup>2</sup> + f<sub>O</sub>) where f<sub>i</sub> = Input Frequency, f<sub>O</sub> = Output Frequency, C<sub>L</sub> = Output Load Capacitance, V<sub>CC</sub> = Supply Voltage.

<sup>(3)</sup>  $C_L = 15pF. V_{CC} = 5.$ (4)  $C_L = 15pF.$ 

#### **6 Parameter Measurement Information**

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O$  = 50  $\Omega$ ,  $t_t$  < 6 ns.

For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.

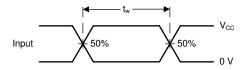


Figure 6-1. Voltage Waveforms, Standard CMOS Inputs Pulse Duration

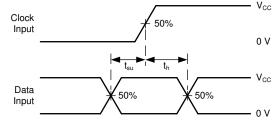


Figure 6-2. Voltage Waveforms, Standard CMOS Inputs Setup and Hold Times

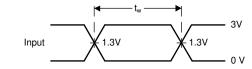


Figure 6-3. Voltage Waveforms, TTL-Compatible CMOS Inputs Pulse Duration

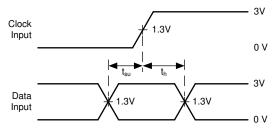


Figure 6-4. Voltage Waveforms, TTL-Compatible CMOS Inputs Setup and Hold Times



#### 7 Detailed Description

#### 7.1 Overview

The 'HC164 and 'HCT164 are 8-bit serial-in parallel-out shift registers with asynchronous reset. Data is shifted on the positive edge of Clock (CLK). A LOW on the Reset (CLR) pin resets the shift register and all outputs go to the LOW state regardless of the input conditions. Two Serial Data inputs (A and B) are provided, either one can be used as a Data Enable control.

#### 7.2 Functional Block Diagram

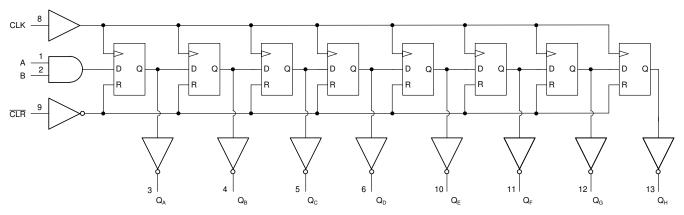


Figure 7-1. Functional Block Diagram

#### 7.3 Device Functional Modes

#### Truth Table<sup>(1)</sup>

OPERATING		INP		OUTPUTS		
MODE	CLR	CLK	CLK A		$Q_A$	Q <sub>B</sub> - Q <sub>H</sub>
RESET (CLEAR)	L	Х	X	X	L	L-L
Shift	Н	1	I	I	L	q <sub>A</sub> - q <sub>F</sub>
	Н	1	I	h	L	q <sub>A</sub> - q <sub>F</sub>
	Н	1	h	I	L	q <sub>A</sub> - q <sub>F</sub>
	Н	1	h	h	Н	q <sub>A</sub> - q <sub>F</sub>

#### (1) H = High voltage level.

h = High voltage level one set-up time prior to the low-to-high clock transition.

I = Low voltage level one set-up time prior to the low-to-high clock transition.

L = Low voltage level.

X = Don't care.

 $\uparrow$  = Transition from low to high level.

 $\ensuremath{q_n}$  = Lower case letters indicate the state of the reference input clock transition.



#### 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V<sub>CC</sub> terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

#### 9 Layout

#### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.



#### 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### **10.1 Documentation Support**

#### 10.1.1 Related Documentation

#### 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 10.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8970401CA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8970401CA CD54HCT164F3A	Samples
CD54HC164F	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC164F	Samples
CD54HC164F3A	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8416201CA CD54HC164F3A	Samples
CD54HCT164F3A	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8970401CA CD54HCT164F3A	Samples
CD74HC164E	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC164E	Samples
CD74HC164M	LIFEBUY	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	_
CD74HC164M96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	Samples
CD74HC164M96G4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	Samples
CD74HC164ME4	LIFEBUY	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	
CD74HC164MT	LIFEBUY	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	
CD74HCT164E	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT164E	Samples
CD74HCT164M96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 125	(HCT164, HCT164M)	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

#### PACKAGE OPTION ADDENDUM

www.ti.com 8-Sep-2023

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF CD54HC164, CD54HC1164, CD74HC164, CD74HC1164:

Catalog: CD74HC164, CD74HCT164

Military: CD54HC164, CD54HCT164

NOTE: Qualified Version Definitions:

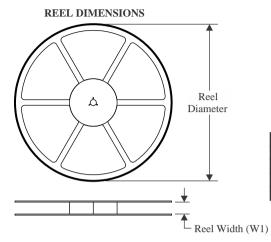
Catalog - TI's standard catalog product

• Military - QML certified for Military and Defense Applications

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#### TAPE AND REEL INFORMATION

NSTRUMENTS



# TAPE DIMENSIONS KO PI BO Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC164M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HC164MT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT164M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT164M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT164M96	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1



www.ti.com 12-May-2023



#### \*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC164M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HC164MT	SOIC	D	14	250	210.0	185.0	35.0
CD74HCT164M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HCT164M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HCT164M96	SOIC	D	14	2500	366.0	364.0	50.0

## **PACKAGE MATERIALS INFORMATION**

www.ti.com 12-May-2023

#### **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HC164E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC164E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC164M	D	SOIC	14	50	506.6	8	3940	4.32
CD74HC164ME4	D	SOIC	14	50	506.6	8	3940	4.32
CD74HCT164E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT164E	N	PDIP	14	25	506	13.97	11230	4.32

CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE



- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
   Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
   Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



## D (R-PDSO-G14)

#### PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



## D (R-PDSO-G14)

## PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



## N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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